General Purpose PIN Photodiodes

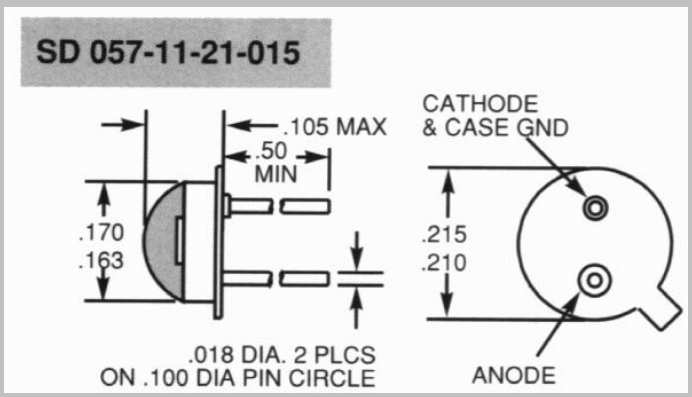
Specifications

Responsivity: 0.32 A/W minimum, 0.36 A/W typical @ 632.8nm; 0.50 A/W minimum, 0.55 A/W typical @ 900 nm

Series Resistance: 100Ω maximum (measured by applying +10mA to photodiode and measuring voltage across anode and cathode)

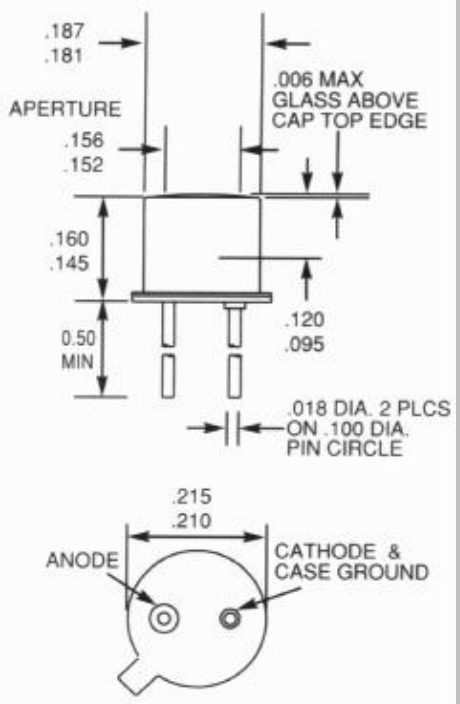
Part Number	Active Area	Storage & Operating Temp.	Shunt Resistance	Dark Current[1] @ 5V		Breakdown Voltage[2] @ 10μ A	Capacitance[3] (typ)		NEP[4]	Max. Linear Current[5]	Response Time[6] @ 10V
	in. (mm)	(C°)	(min) (M-Ohm)	(typ) (nA)	(max) (nA)	(typ) (V)	at 0V (pF)	at 5V (pF)	(typ) (W/√ Hz)	(typ) (mA)	(typ) (nsec)
SD 057-11-21-015	0.051 x 0.051 (1.3 x 1.3)	-20 to 75	800	0.5	2.0	50	28	6	$2.8x10^{-14}$	0.17	7
SD 057-11-21-011	0.051 x 0.051 (1.3 x 1.3)	-40 to 110	800	0.5	2.0	50	28	6	$2.8x10^{-14}$	0.17	7
SD 076-11-21-011 (isolated) –211	0.105 x 0.043 (2.66 x 1.09)	-40 to 110	450	0.9	3.5	50	50	10	$3.2x10^{-14}$	0.29	8
SD 100-11-21-021 (isolated) -221	0.100 (dia.) (2.54 dia.)	-40 to 110	300	1.6	6.4	50	87	18	$4.0x10^{-14}$	0.51	10
SD 125-11-21-021	0.111 x 0.111 (2.8 x 2.8)	-40 to 110	180	2.5	10.0	50	135	28	$5.2x10^{-14}$	0.80	15
SD 172-11-21-021 (isolated) –221	0.185 x 0.125 (4.7 x 3.18)	-40 to 110	100	5.0	20.0	50	255	53	$7.0x10^{-14}$	1.5	30
SD 200-11-21-041 (isolated) –241	0.200 (dia.) (5.08 dia.)	-40 to 110	70	6.5	26.0	50	345	71	$8.6x10^{-14}$	2.03	32
SD 290-11-21-041 (isolated) –241	0.300 x 0.220 (7.62 x 5.58)	-40 to 110	35	13.0	52.0	50	725	150	$1.2x10^{-13}$	4.26	70
SD 445-11-21-305	0.394 x 0.394 (10 x 10)	-20 to 75	15	30.0	120	50	1700	350	$2.0x10^{-13}$	10.0	140

1. Dark Current and Shunt Resistance vary with temperature as follows: for T>23° C, $I_D=1.09^{\Delta T} I_{D23}$, $R_{SH}=0.9^{\Delta T} R_{SH23}$ and for T<23° C, $I_D=I_{D23}/1.09^{\Delta T}$, $R_{SH}=R_{SH23}/0.9^{\Delta T}$, where Δ T is the temperature difference from 23° C, and I_{D23} and R_{SH23} are the dark current and shunt resistance at 23° C.
2. Typical values listed. Minimum value shall be 50% of typical.
3. Typical values are listed in the table. Maximum value is 20% higher than the typical value.
4. Test conditions are V_B=5V and 950nm.
5. Maximum linear current specifies the level above which the output current deviates more than 10%. Short circuit current saturates at approximately 10 times this level.
6. Response times listed are for the rising or falling edge, and were measured at 830nm with a 50W load. Shorter wavelengths will result in faster rise and fall times.

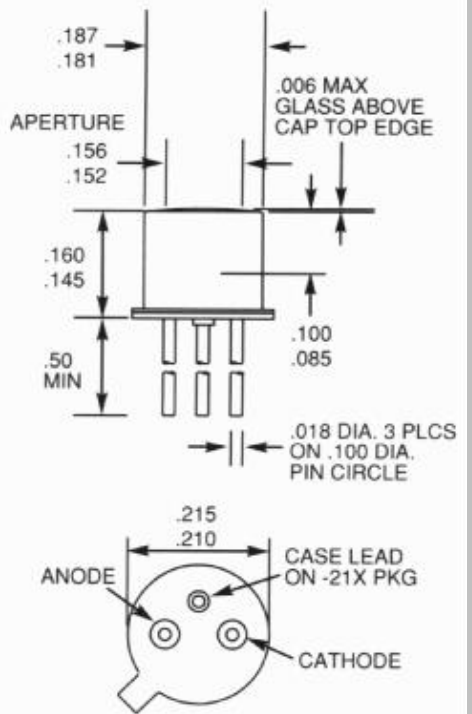


SD 057-11-21-011

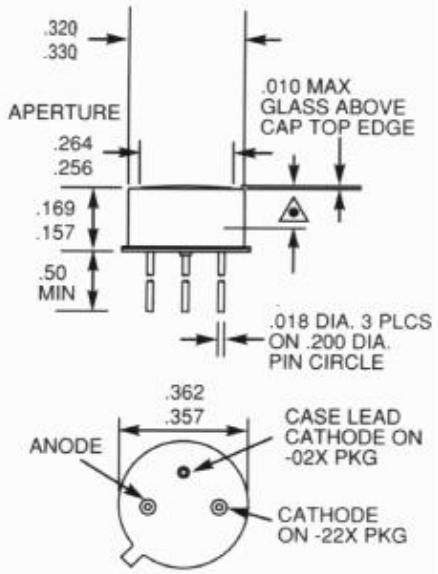
SD 076-11-21-011



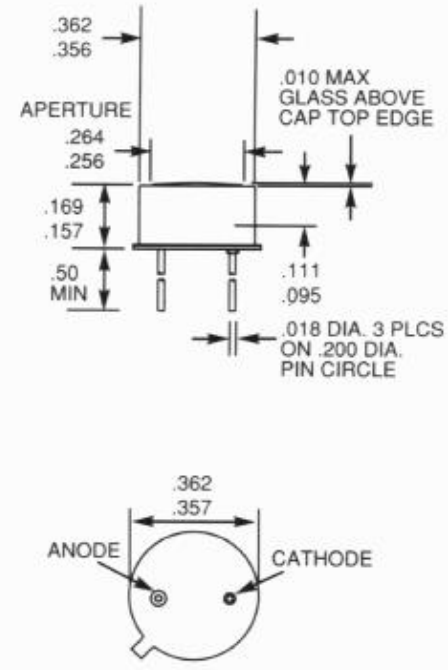
SD 076-11-21-211



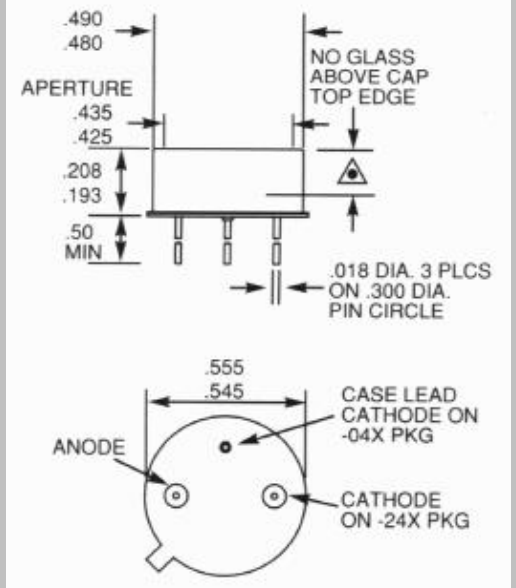
	▲
SD 100-11-21-021	.111 .095
SD 100-11-21-221	.098 .078
SD 172-11-21-021	.111 .095
SD 172-11-21-221	.098 .078



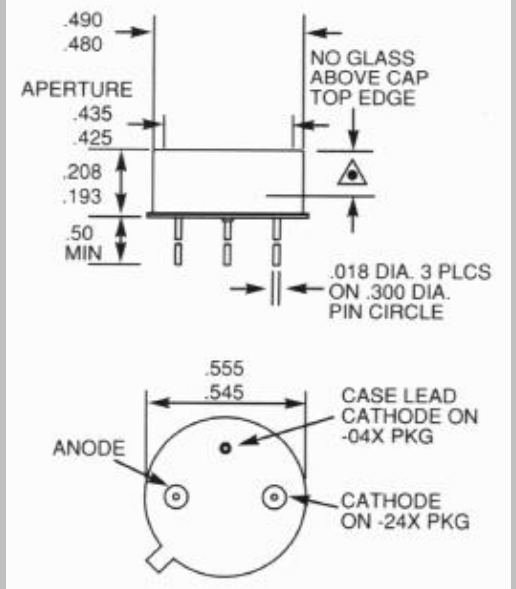
SD 125-11-21-021



	△
SD 200-11-21-041	.136 .095
SD 200-11-21-241	.111 .115
SD 290-11-21-041	.136 .095
SD 290-11-21-241	.111 .115



	△
SD 200-11-21-041	.136 .095
SD 200-11-21-241	.111 .115
SD 290-11-21-041	.136 .095
SD 290-11-21-241	.111 .115



SD 445-11-21-305